

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

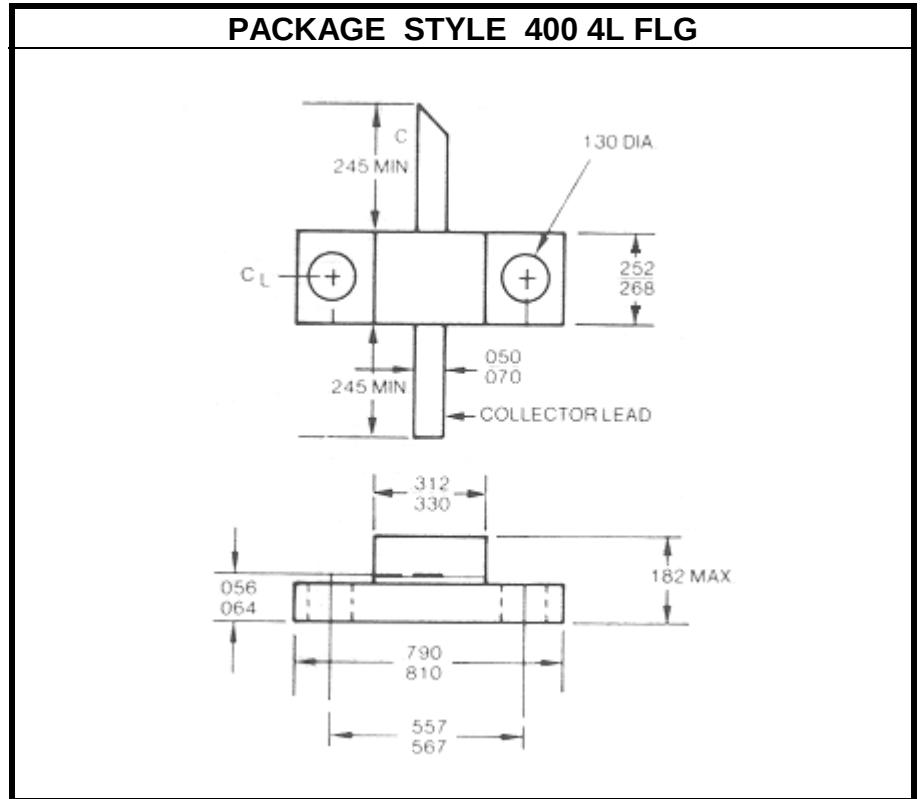
The **ASI MRAL1720-9** is Designed for Class C, Common Base Wideband Large Signal Amplifier Applications up to 2.0 GHz.

FEATURES:

- Diffused Ballast Resistors.
- Internal Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A (CONT)
V_{CES}	42 V
V_{EBO}	3.5 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.5 °C/W



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 80 mA	42			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CBO}	V _{CB} = 22 V			2.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 400 mA	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			12	pF
G_{PB}	V _{CE} = 22 V P _{out} = 9.0 W f = 1.7 GHz & 2.0 GHz	6.5			dB
η_C		40			%